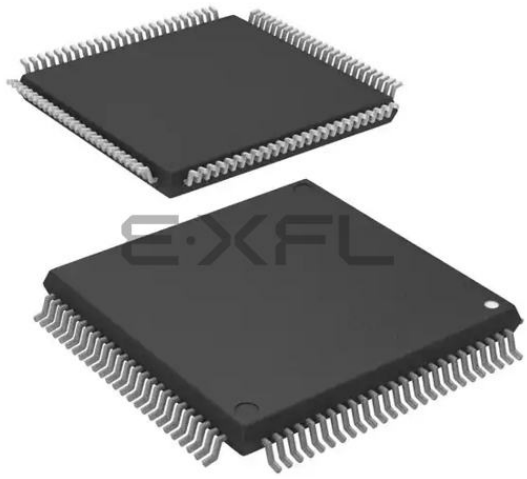
Renesas Electronics America Inc - R5F110PEAFB#30 Datasheet



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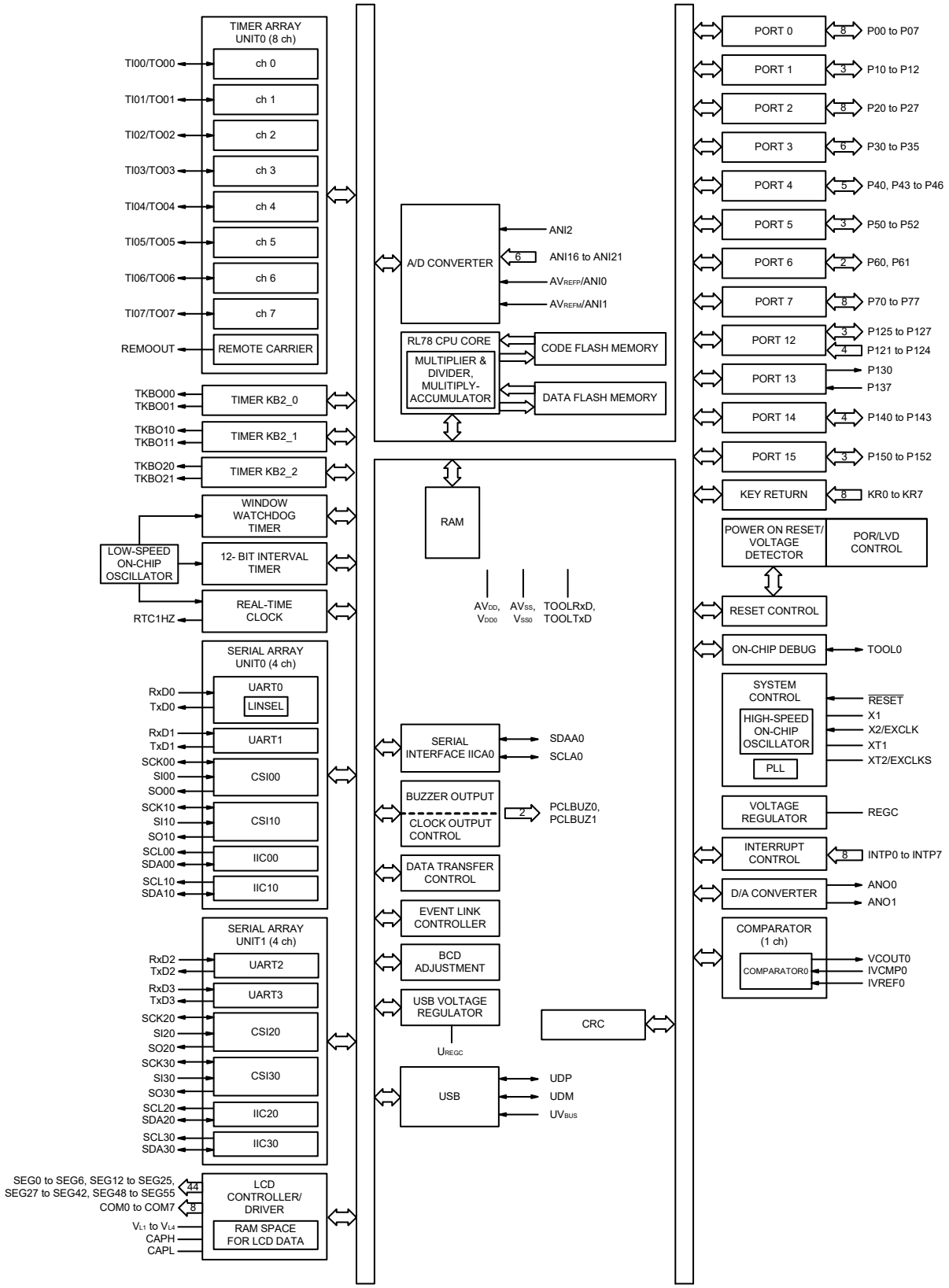
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

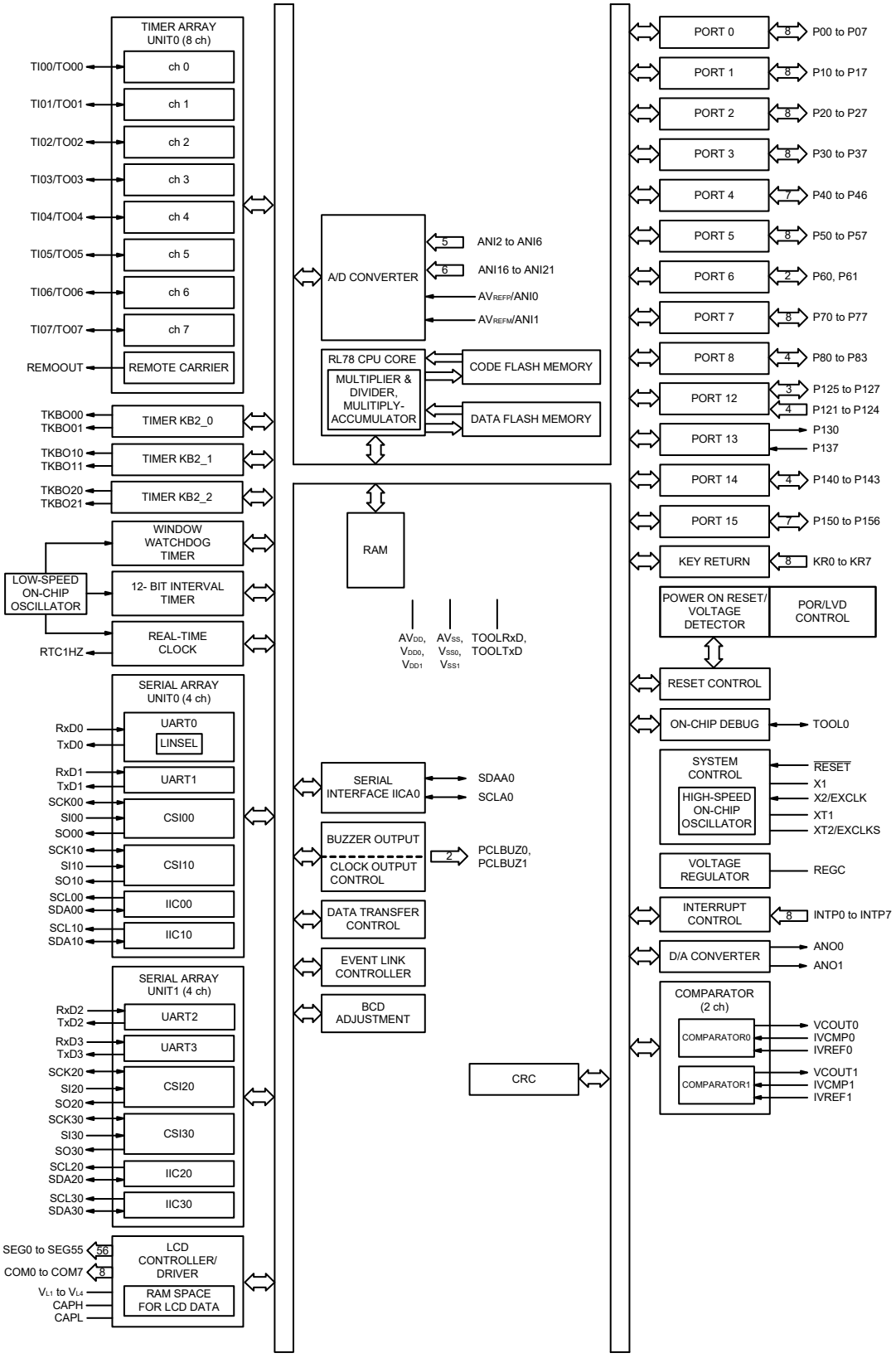
Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART, USB
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	69
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 13x8/12b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f110peafb-30

1.5 Block Diagram

1.5.1 80/85-pin products (with USB)



1.5.4 100-pin products (without USB)



Absolute Maximum Ratings (T_A = 25°C) (2/3)

Parameter	Symbols	Conditions		Ratings	Unit
LCD voltage	V_{LI1}	V_{L1} input voltage Note 1		-0.3 to +2.8	V
	V_{LI2}	V_{L2} input voltage Note 1		-0.3 to +6.5	V
	V_{LI3}	V_{L3} input voltage Note 1		-0.3 to +6.5	V
	V_{LI4}	V_{L4} input voltage Note 1		-0.3 to +6.5	V
	V_{LI5}	CAPL, CAPH input voltage Note 1		-0.3 to +6.5	V
	V_{LO1}	V_{L1} output voltage		-0.3 to +2.8	V
	V_{LO2}	V_{L2} output voltage		-0.3 to +6.5	V
	V_{LO3}	V_{L3} output voltage		-0.3 to +6.5	V
	V_{LO4}	V_{L4} output voltage		-0.3 to +6.5	V
	V_{LO5}	CAPL, CAPH output voltage		-0.3 to +6.5	V
	V_{LO6}	COM0 to COM7 SEG0 to SEG55 output voltage	External resistance division method	-0.3 to V_{DD} + 0.3 Note 2	V
			Capacitor split method	-0.3 to V_{DD} + 0.3 Note 2	V
			Internal voltage boosting method	-0.3 to V_{LI4} + 0.3 Note 2	V

Note 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to V_{SS} via a capacitor (0.47 ± 30%) and connect a capacitor (0.47 ± 30%) between the CAPL and CAPH pins.

Note 2. Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

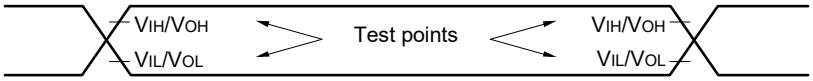
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0.8 V_{DD}		V_{DD}	V
	V_{IH2}	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	2.0		V_{DD}	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	1.50		V_{DD}	V
	V_{IH3}	P150 to P156		0.7 AV_{DD}		AV_{DD}	V
	V_{IH4}	P60, P61		0.7 V_{DD}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0		0.2 V_{DD}	V
	V_{IL2}	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	0		0.5	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P150 to P156		0		0.3 AV_{DD}	V
	V_{IL4}	P60, P61		0		0.3 V_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.7 V ≤ V_{DD} ≤ 3.6 V		f_{MCK}/6 Note 2		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps
		2.4 V ≤ V_{DD} ≤ 3.6 V		f_{MCK}/6 Note 2		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		2.6		1.3		0.6	Mbps
		1.8 V ≤ V_{DD} ≤ 3.6 V	—			f_{MCK}/6 Note 2		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3	—			1.3		0.6	Mbps
		1.6 V ≤ V_{DD} ≤ 3.6 V	—		—			f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3	—		—			0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The following conditions are required for low voltage interface.
2.4 V ≤ V_{DD} < 2.7 V: MAX. 2.6 Mbps
1.8 V ≤ V_{DD} < 2.4 V: MAX. 1.3 Mbps
1.6 V ≤ V_{DD} < 1.8 V: MAX. 0.6 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 3.6 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 3.6 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(5) During communication at same potential (simplified I²C mode)

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		—		—		250	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		1850		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		1850		ns
Data setup time (reception)	$t_{SU: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 85 Note 2		1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1/f_{MCK} + 230 Note 2		1/f_{MCK} + 230 Note 2		1/f_{MCK} + 230 Note 2		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		1/f_{MCK} + 290 Note 2		ns
Data hold time (transmission)	$t_{HD: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		0	405	ns

Note 1. The value must be equal to or less than f_{MCK}/4.

Note 2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(8) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	177		479		479		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		195		195		195	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		483		483		483	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

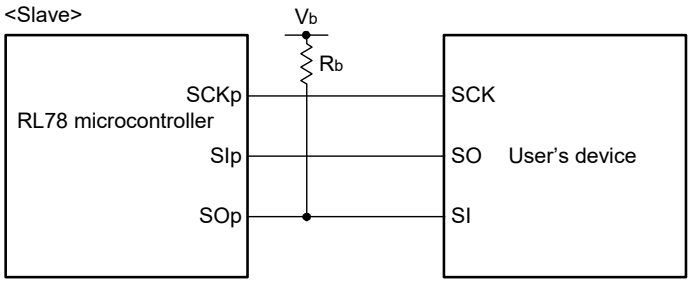
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with V_{DD} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

(3) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI0 to ANI6

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±7.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.375			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{DD} ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{DD} ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	2.5625			
			1.8 V ≤ AV_{DD} ≤ 3.6 V	5.125			
			1.6 V ≤ AV_{DD} ≤ 3.6 V	10.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Analog input voltage	VAIN	ANI0 to ANI6		0		AV_{DD}	V

Note 1. Cannot be used for lower 2 bit of ADCR register

Note 2. Cannot be used for lower 4 bit of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(4) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ AVREFP ≤ AVDD = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.3125			
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	7.875			
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	54.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Analog input voltage	VAIN			0		AVREFP	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 4			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AVDD pin with the same potential as the V_{DD} pin.

(2) 1/4 bias method

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} - 0.08	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} - 0.12	3 V_{L1}	3 V_{L1}	V
Quadruply output voltage	V_{L4}	C1 to C5 Note 1 = 0.47 μF		4 V_{L1} - 0.16	4 V_{L1}	4 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C5 Note 1 = 0.47μF		500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C5: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(T_A = -40 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH1} = -2.0 mA	V_{DD} - 0.6			V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OH1} = -1.5 mA	V_{DD} - 0.5			V
	V_{OH2}	P150 to P156	2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OH2} = -100 μA	AV_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P130, P140 to P143	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 3.0 mA			0.6	V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 1.5 mA			0.4	V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 0.6 mA			0.4	V
	V_{OL2}	P150 to P156	2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL3} = 3.0 mA			0.4	V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL3} = 2.0 mA			0.4	V

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the real-time clock 2, 12-bit interval timer, and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz
2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 48 MHz Note 4, f_{IH} = 24 MHz Note 4	V_{DD} = 3.6 V		0.77	3.4	mA
					V_{DD} = 3.0 V		0.77	3.4	
				f_{HOCO} = 24 MHz Note 4, f_{IH} = 24 MHz Note 4	V_{DD} = 3.6 V		0.55	2.7	
					V_{DD} = 3.0 V		0.55	2.7	
				f_{HOCO} = 16 MHz Note 4, f_{IH} = 16 MHz Note 4	V_{DD} = 3.6 V		0.48	1.9	
					V_{DD} = 3.0 V		0.47	1.9	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.35	2.10	mA
					Resonator connection		0.51	2.20	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.34	2.10	
					Resonator connection		0.51	2.20	
				f_{MX} = 16 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.30	1.25	
					Resonator connection		0.45	1.41	
				f_{MX} = 16 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.29	1.23	
					Resonator connection		0.45	1.41	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.23	1.10	
					Resonator connection		0.30	1.20	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.22	1.10	
					Resonator connection		0.30	1.20	
			HS (High-speed main) mode (PLL operation)	f_{MX} = 48 MHz, f_{CLK} = 24 MHz Note 3	V_{DD} = 3.6 V		0.99	2.93	mA
					V_{DD} = 3.0 V		0.99	2.92	
				f_{MX} = 48 MHz, f_{CLK} = 12 MHz Note 3	V_{DD} = 3.6 V		0.89	2.51	
					V_{DD} = 3.0 V		0.89	2.50	
				f_{MX} = 48 MHz, f_{CLK} = 6 MHz Note 3	V_{DD} = 3.6 V		0.84	2.30	
					V_{DD} = 3.0 V		0.84	2.29	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5 T_A = -40°C	Square wave input		0.32	0.61	μA
					Resonator connection		0.51	0.80	
				f_{SUB} = 32.768 kHz Note 5 T_A = +25°C	Square wave input		0.41	0.74	
					Resonator connection		0.62	0.91	
				f_{SUB} = 32.768 kHz Note 5 T_A = +50°C	Square wave input		0.52	2.30	
					Resonator connection		0.75	2.49	
				f_{SUB} = 32.768 kHz Note 5 T_A = +70°C	Square wave input		0.82	4.03	
					Resonator connection		1.08	4.22	
				f_{SUB} = 32.768 kHz Note 5 T_A = +85°C	Square wave input		1.38	8.04	
					Resonator connection		1.62	8.23	
				f_{SUB} = 32.768 kHz Note 5 T_A = +105°C	Square wave input		3.29	41.00	
					Resonator connection		3.63	41.00	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.18	0.52	μA
			T_A = +25°C				0.25	0.52	
			T_A = +50°C				0.34	2.21	
			T_A = +70°C				0.64	3.94	
			T_A = +85°C				1.18	7.95	
			T_A = +105°C				2.92	40.00	

(**Notes** and **Remarks** are listed on the next page.)

3.4 AC Characteristics

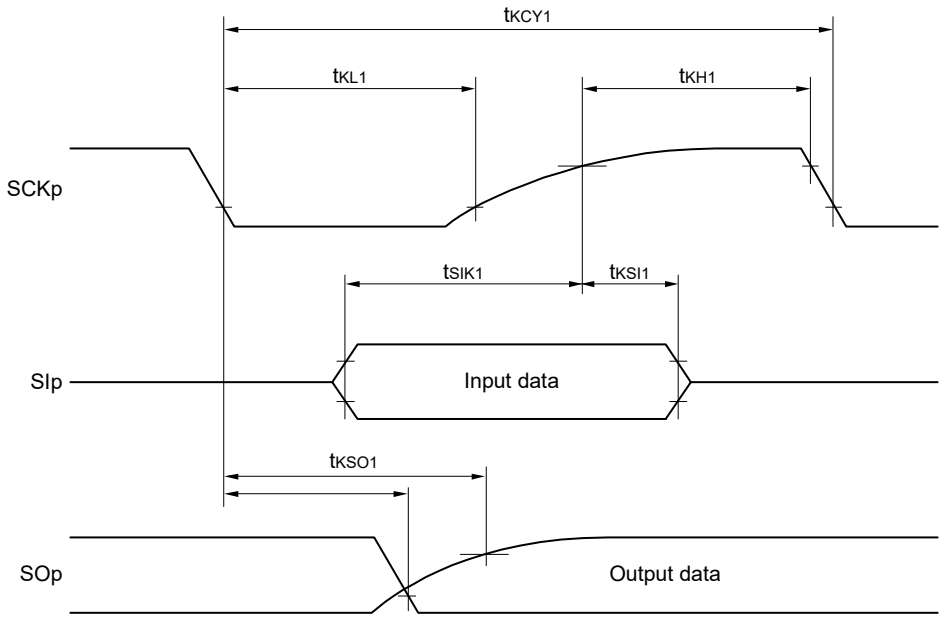
3.4.1 Basic operation

(T_A = -40 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(1/2)**

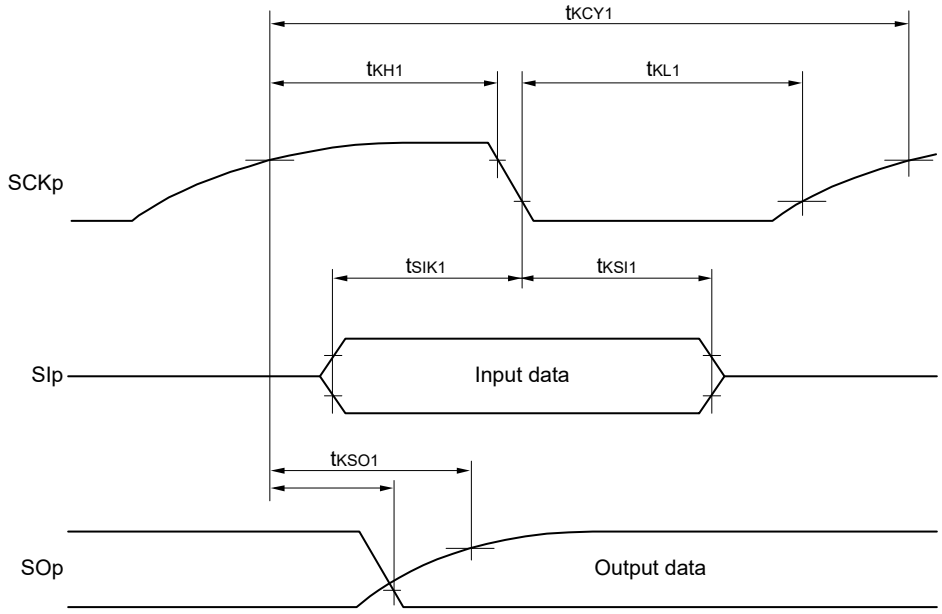
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f_{SUB}) operation		2.4 V ≤ V_{DD} ≤ 3.6 V	28.5	30.5	31.3	μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 3.6 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
	f_{EXT}				32		35	kHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 3.6 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 7))

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

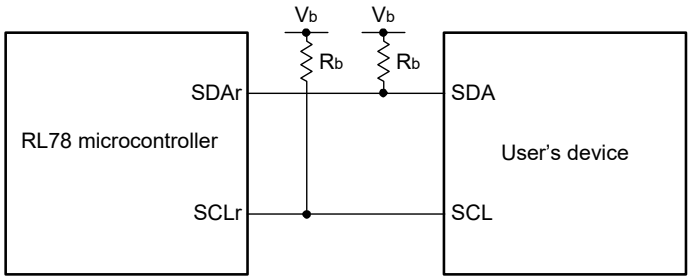


CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

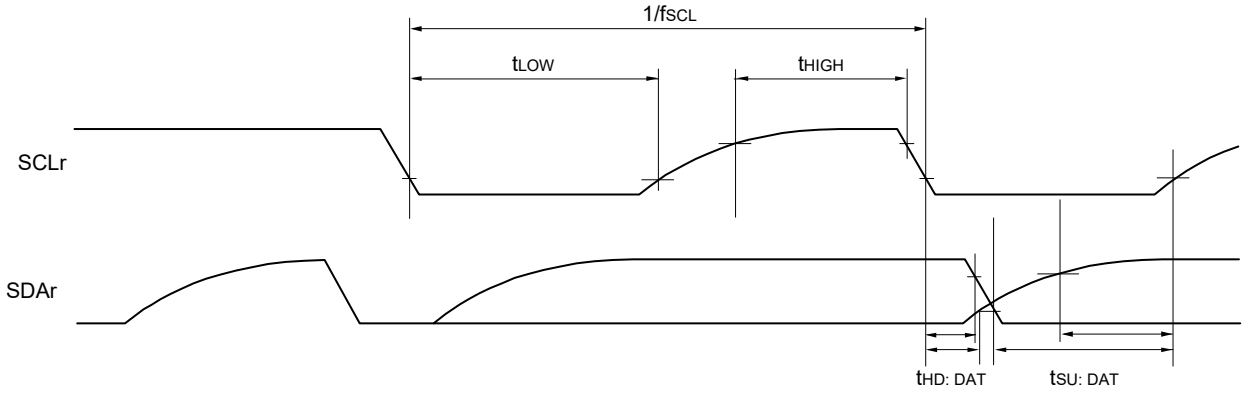


Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM number (g = 0 to 3)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM, POM number (g = 0 to 3)

Remark 3. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00, 02, 10, 12)

3.6.6 LVD circuit characteristics

(T_A = -40 to +105°C, $V_{PDR} \leq V_{DD} \leq 3.6$ V $\leq V_{SS}$ = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		VLVD3	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V_{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V_{LVD5}	Power supply rise time	2.71	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V_{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V_{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

Caution Set the detection voltage (V_{LVD}) to be within the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H/010C2H). The following shows the operating voltage range.
HS (high-speed main) mode: V_{DD} = 2.7 to 3.6 V at 1 MHz to 24 MHz
V_{DD} = 2.4 to 3.6 V at 1 MHz to 16 MHz

3.8.3 Capacitor split method

(1) 1/3 bias method

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V_{L4} voltage	V_{L4}	C1 to C4 = 0.47 μF Note 2		V_{DD}		V
V_{L2} voltage	V_{L2}	C1 to C4 = 0.47 μF Note 2	2/3 V_{L4} - 0.07	2/3 V_{L4}	2/3 V_{L4} + 0.07	V
V_{L1} voltage	V_{L1}	C1 to C4 = 0.47 μF Note 2	1/3 V_{L4} - 0.08	1/3 V_{L4}	1/3 V_{L4} + 0.08	V
Capacitor split wait time Note 1	t_{VWAIT}		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

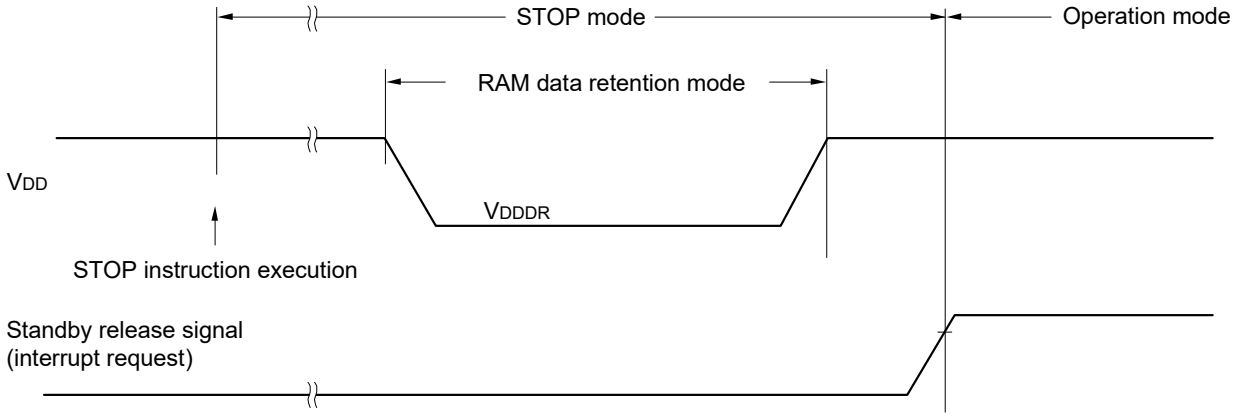
Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

3.9 RAM Data Retention Characteristics

(T_A = -40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		3.6	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.